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ABSTRACT OF THE DISCLOSURE

A fuse for use in semiconductor devices, semiconductor devices including the fuse, methods of fabricating the fuse, and method of using the fuse. The fuse includes terminal ends and a central region disposed between the terminal ends. The central
5 region of the fuse may have a narrower width than the terminal ends of the fuse. The terminal ends each include two layers of conductive material disposed on an insulative substrate. The central region includes a single layer of conductive material, which is substantially continuous with the upper of the two layers of conductive material of the terminal ends of the fuse. The layer of conductive material adjacent the insulative
10 substrate may comprise polysilicon, while the other layer of conductive material may comprise a metal silicide. When such materials are employed, the fuse may be fabricated substantially concurrently with the fabrication of a conventional metal silicide transistor gate structure on a semiconductor device, requiring only one additional patterning process. Since the central region of the fuse has a lesser conductive material volume than
15 the terminal ends thereof, the central region of the fuse may be more readily "blown" than the terminal ends thereof.

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